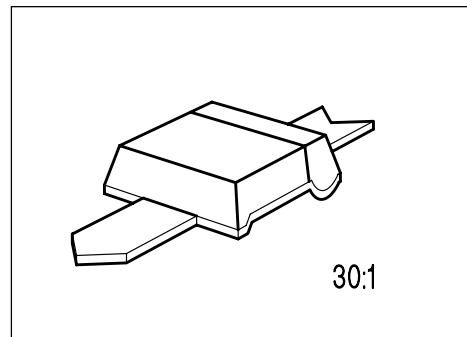


Silicon Schottky Diodes

BAT 14- ... S

- Beam lead technology
- Low dimension
- High performance
- Medium barrier



ESD: Electrostatic discharge sensitive device, observe handling precautions!

Type	Marking	Ordering Code	Pin Configuration	Package ¹⁾
BAT 14-020 S	–	Q62702-D1258	Pointed cathode 	S
BAT 14-050 S		Q62702-D1267		
BAT 14-090 S		Q62702-D1275		
BAT 14-110 S		Q62702-D1284		

Maximum Ratings

Parameter	Symbol	Values		Unit
		BAT 14-020 S BAT 14-050 S	BAT 14-090 S BAT 14-110 S	
Reverse voltage	V_R	4	4	V
Forward current	I_F	100	50	mA
Junction temperature	T_j	175		°C
Storage temperature range	T_{stg}	− 65 ... + 150		
Operating temperature range	T_{op}	− 65 ... + 150		

¹⁾ For detailed information see chapter Package Outlines.

Electrical Characteristics

at $T_A = 25\text{ °C}$, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

DC Characteristics

Breakdown voltage $I_R = 10\text{ }\mu\text{A}$	$V_{(BR)}$	4	—	—	V
Diode capacitance $V_R = 0, f = 1\text{ MHz}$	C_T	—	0.30	0.35	pF
BAT 14-020 S		—	0.20	0.25	
BAT 14-050 S		—	0.14	0.15	
BAT 14-090 S		—	0.10	0.12	
BAT 14-110 S		—			
Forward voltage $I_F = 1\text{ mA}$	V_F	—	0.45	—	V
BAT 14-020 S		—	0.47	—	
BAT 14-050 S		—	0.49	—	
BAT 14-090 S		—	0.50	—	
BAT 14-110 S		—	0.55	—	
$I_F = 10\text{ mA}$		—	0.57	—	
BAT 14-020 S		—	0.60	—	
BAT 14-050 S		—	0.65	—	
BAT 14-090 S		—			
BAT 14-110 S		—			
Single sideband noise figure $F_{IF} = 1.5\text{ dB}, P_{LO} = 0\text{ dBm}, f_{IF} = 10.7\text{ MHz}$	F_{SSB}	—	6.0	—	dB
$f = 3.0\text{ GHz}$		—	6.5	—	
$f = 6.0\text{ GHz}$		—	6.5	—	
$f = 9.3\text{ GHz}$		—	7.0	—	
$f = 16\text{ GHz}$		—			
Differential forward resistance $I_F = 10\text{ mA}$	r_f	—	3.5	—	Ω
BAT 14-020 S		—	4.0	—	
BAT 14-050 S		—	7.0	—	
BAT 14-090 S		—	10.0	—	
BAT 14-110 S		—			